

TRANSISTOR (PNP)

Plastic-Encapsulate Transistor

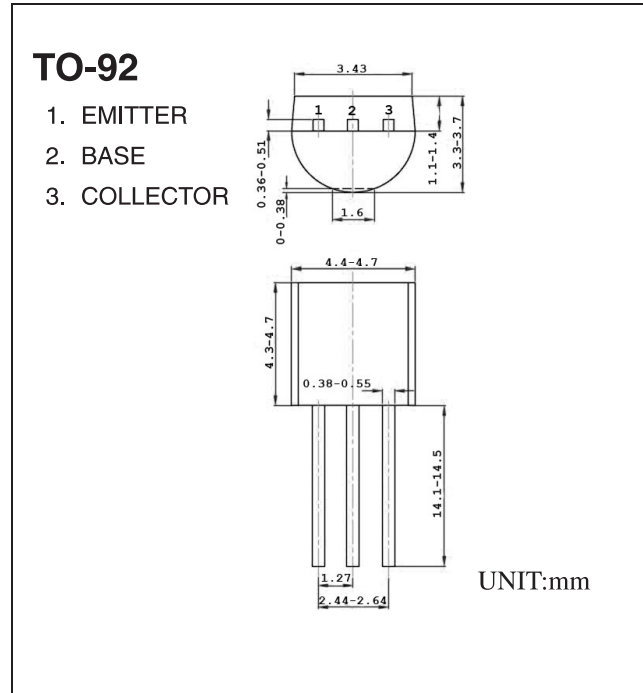
FEATURES

Power dissipation
 P_{CM} : 1W ($T_{amb}=25^{\circ}C$)

Collector current
 I_{CM} : -1.5A

Collector-base voltage
 $V_{(BR)CBO}$: -40V

Operating and storage junction temperature range
 T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS
 Ratings at $25^{\circ}C$ ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100 \mu A, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-0.1mA, I_B=0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100 \mu A, I_C=0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V, I_E=0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-20V, I_B=0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-100mA$	85	300	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-800mA$	40		
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-800mA, I_B=-80mA$		-0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=-800mA, I_B=-80mA$		-1.2	V
Base-emitter voltage	V_{BE}	$I_E=-1.5A$		-1.6	V
Transition frequency	f_r	$V_{CE}=-10V, I_C=-50mA$ $f=30MHz$	190		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C	D
Range	85-160	120-200	160-300